# MCH3476

# Power MOSFET 20V, 125mΩ, 2A, Single N-Channel

# **Features**

- Low On-Resistance
- 1.8V Drive
- ESD Diode-Protected Gate
- Pb-Free, Halogen Free and RoHS Compliance

# **Specifications**

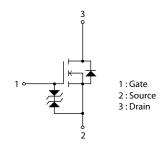
# Absolute Maximum Ratings at $Ta = 25^{\circ}C$

Parameter	Symbol	Value	Unit
Drain to Source Voltage	VDSS	20	V
Gate to Source Voltage	VGSS	±12	V
Drain Current (DC)	ID	2	А
Drain Current (Pulse) PW≤10µs, duty cycle≤1%	I <sub>DP</sub>	8	А
Power Dissipation When mounted on ceramic substrate (900mm <sup>2</sup> × 0.8mm)	PD	0.8	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	–55 to +150	°C

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VDSS	R <sub>DS</sub> (on) Max	ID Max
	125mΩ@ 4.5V	
20V	190mΩ@ 2.5V	2A
	310mΩ@ 1.8V	



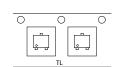


Packing Type : TL

Marking

### **Thermal Resistance Ratings**

Parameter	Symbol	Value	Unit
Junction to Ambient When mounted on ceramic substrate (900mm <sup>2</sup> × 0.8mm)	R <sub>θJA</sub>	156.2	°C/W





Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### **ORDERING INFORMATION**

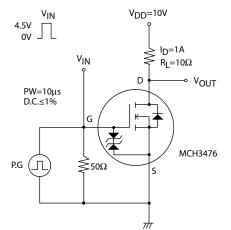
See detailed ordering and shipping information on page 5 of this data sheet.

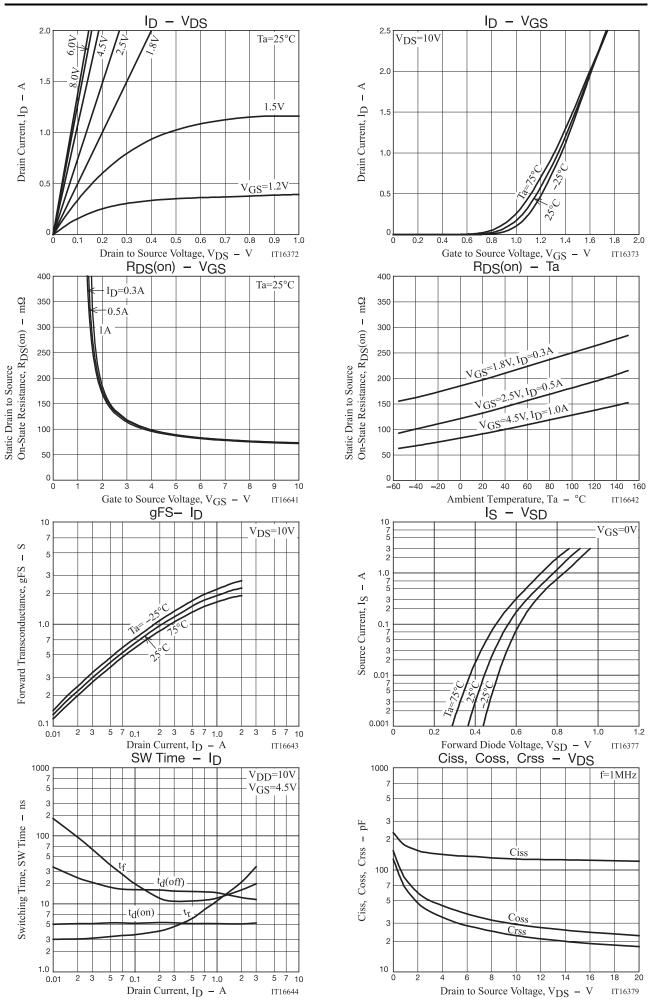
## **Electrical Characteristics** at $Ta = 25^{\circ}C$

Parameter	Symbol	Conditions		Value		
			min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	I <sub>D</sub> =1mA, V <sub>GS</sub> =0V	20			V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V			1	μΑ
Gate to Source Leakage Current	IGSS	$V_{GS}=\pm 8V$ , $V_{DS}=0V$			±10	μΑ
Gate Threshold Voltage	V <sub>GS</sub> (th)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	0.4		1.3	V
Forward Transconductance	9FS	V <sub>DS</sub> =10V, I <sub>D</sub> =1A		1.9		S
Static Drain to Source On-State Resistance	R <sub>DS</sub> (on)1	I <sub>D</sub> =1A, V <sub>GS</sub> =4.5V		93	125	mΩ
	R <sub>DS</sub> (on)2	I <sub>D</sub> =0.5A, V <sub>GS</sub> =2.5V		135	190	mΩ
	R <sub>DS</sub> (on)3	I <sub>D</sub> =0.3A, V <sub>GS</sub> =1.8V		200	310	mΩ
Input Capacitance	Ciss	V <sub>DS</sub> =10V, f=1MHz		128		pF
Output Capacitance	Coss			28		pF
Reverse Transfer Capacitance	Crss			21		pF
Turn-ON Delay Time	t <sub>d</sub> (on)	See specified Test Circuit		5.1		ns
Rise Time	tr			11		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)			14.5		ns
Fall Time	tf	7		12		ns
Total Gate Charge	Qg	V <sub>DS</sub> =10V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =2A		1.8		nC
Gate to Source Charge	Qgs			0.3		nC
Gate to Drain "Miller" Charge	Qgd	1		0.55		nC
Forward Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> =2A, V <sub>GS</sub> =0V		0.85	1.2	V

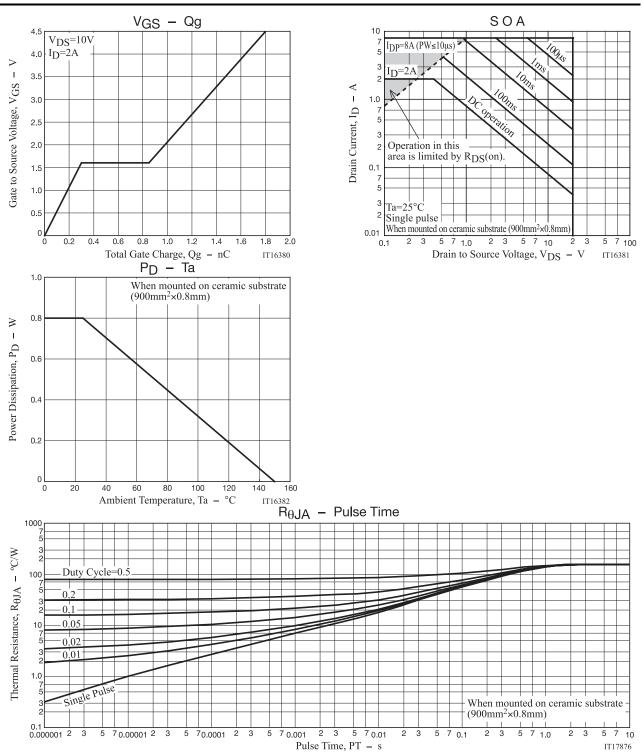
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

# **Switching Time Test Circuit**





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# Package Dimensions

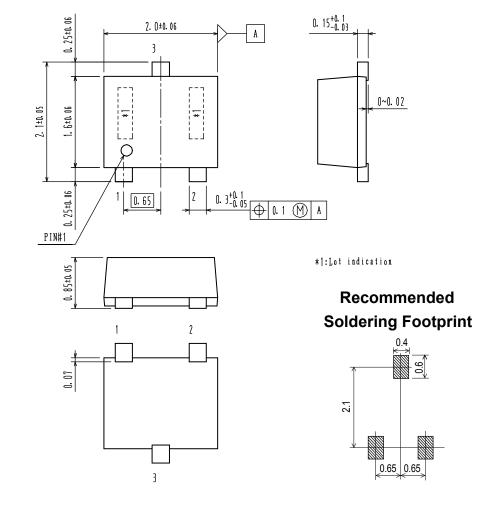
MCH3476-TL-H / MCH3476-TL-W

## MCPH3

CASE 419AQ ISSUE O

unit : mm

- 1 : Gate
- 2 : Source
- 3 : Drain



# **ORDERING INFORMATION**

Device	Package	Shipping	Note	
MCH3476-TL-H	MCPH3	3,000 pcs. / Tape & Reel	Pb-Free	
MCH3476-TL-W	SC-70FL, SOT-323	3,000 pcs. / Tape & Reel	and Halogen Free	

+ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub\_link/Collateral/BRD8011-D.PDF

# Note on usage : Since the MCH3476 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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